

Notice of References Cited

Application/Control No.

10/046,259

Applicant(s)/Patent Under
Reexamination
NAKAGAWA ET AL.

Examiner

Paul D Kim

Art Unit

3729

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,088,462	07-2000	Fujimoto et al.	381/160
	B	US-5,929,723	07-1999	Kimura et al.	333/193
	C	US-5,281,485	01-1994	Colgan et al.	428/457
	D	US-5,221,449	06-1993	Colgan et al.	204/192.15
	E	US-4,410,867	10-1983	Arcidiacono et al.	333/172
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	I	US-			
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	K	US-			
	L	US-			
	M	US-			

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	N	JP 04186815 A	07-1992	Japan	FUKURODA et al.	H01L 21/02
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NON-PATENT DOCUMENTS

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	U	"Low-resistivity PVD /spl alpha/-tantalum: phase formation and integration in ultra-low k dielectric/copper damascene structures Donohue, H.; Gris, H.; Yeoh, J.C.; Buchanan, K.; Interconnect Technology Conference, IEEE 2002; Pages:179 - 181.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.